

Title (en)

As/P HYBRID nLDD JUNCTION AND MEDIUM V_{dd} OPERATION FOR HIGH SPEED MICROPROCESSORS

Title (de)

HYBRIDER As/P-nLDD-ÜBERGANG UND MITTLERE V_{dd}-FUNKTIONSWEISE FÜR HOCHGESCHWINDIGKEITSMIKROPROZESSOREN

Title (fr)

JONCTION A ZONES nLDD HYBRIDES As/P AVEC FONCTIONNEMENT A TENSION D'ALIMENTATION MOYENNE POUR MICROPROCESSEURS A GRANDE VITESSE

Publication

EP 0966762 A1 19991229 (EN)

Application

EP 98904623 A 19980121

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Abstract (en)

[origin: WO9832176A1] A method of manufacturing a semiconductor device wherein hybrid nLDD regions are formed by implanting arsenic ions and phosphorous ions in source and drain regions of a substrate. The source and drain regions are formed by implanting either arsenic or phosphorous ions.

IPC 1-7

H01L 29/78; H01L 21/336

IPC 8 full level

H01L 21/336 (2006.01); **H01L 29/78** (2006.01)

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See references of WO 9832176A1

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